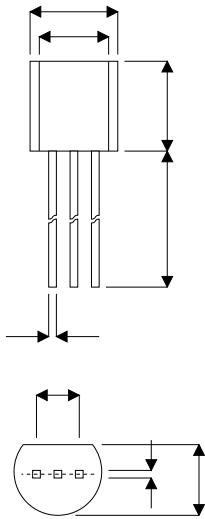


**MECHANICAL DATA**

Dimensions in mm (inches)



**TO92 PACKAGE**

PIN 1 – Drain      PIN 2 – Gate      PIN 3 – Drain

**N-CHANNEL  
ENHANCEMENT MODE  
MOS TRANSISTOR**

**FEATURES**

- $V_{(BR)DSS} = 60V$
- $R_{DS(ON)} = 5\Omega$
- $I_D = 1A$

**ABSOLUTE MAXIMUM RATINGS** ( $T_{CASE} = 25^\circ C$  unless otherwise stated)

|                |   |              |
|----------------|---|--------------|
| $V_{DS}$       | Drain – Source Voltage  | 60V          |
| $V_{GS}$       | Gate – Source Voltage   | $\pm 40V$    |
| $I_D$          | Drain Current   | 200mA        |
| $I_{DM}$       | Pulsed Drain Current  | 500mA        |
| $P_D$          | Power Dissipation   | 400mW        |
|                | Derate above 25°C   | 3.2mW/°C     |
| $T_j, T_{stg}$ | Operating and Storage Temperature Range   | -55 to 150°C |
| $T_L$          | Maximum Lead Temperature for Soldering Purposes,<br>1/16 from case for 10 seconds | 300°C        |

**ELECTRICAL CHARACTERISTICS** ( $T_{CASE} = 25^{\circ}C$  unless otherwise stated)

| Parameter                        | Test Conditions                     | Min.              | Typ.                 | Max.                      | Unit |            |          |
|----------------------------------|-------------------------------------|-------------------|----------------------|---------------------------|------|------------|----------|
| <b>STATIC CHARACTERISTICS</b>    |                                     |                   |                      |                           |      |            |          |
| $V_{(BR)DSS}$                    | Gate – Source Breakdown Voltage     | $V_{GS} = 0V$     | $I_D = 10\mu A$      | 60                        |      | V          |          |
| $V_{GS(th)}$                     | Gate Threshold Voltage              | $V_{DS} = V_{GS}$ | $I_D = 1mA$          | 0.8                       | 3.0  |            |          |
| $I_{GSS}$                        | Gate – Body Leakage Current Forward | $V_{GSF} = 15V$   | $V_{DS} = 0V$        |                           | -10  | nA         |          |
| $I_{DSS}$                        | Zero Gate Voltage Drain Current     | $V_{DS} = 48V$    | $V_{GS} = 0V$        |                           | 1    | $\mu A$    |          |
|                                  |                                     |                   | $T_J = 125^{\circ}C$ |                           | 1    | mA         |          |
| $I_{D(on)*}$                     | On–State Drain Current              | $V_{GS} = 4.5$    | $V_{DS} = 10V$       | 75                        |      | mA         |          |
| $R_{DS(on)*}$                    | Drain – Source On Resistance        | $V_{GS} = 10V$    | $I_D = 0.5A$         | $T_{CASE} = 125^{\circ}C$ |      | 5          | $\Omega$ |
|                                  |                                     |                   |                      |                           |      | 9          |          |
| $V_{DS(on)*}$                    | Drain – Source On Voltage           | $V_{GS} = 10V$    | $I_D = 0.5A$         |                           | 2.5  | V          |          |
|                                  |                                     |                   | $V_{GS} = 4.5V$      | $I_D = 75mA$              |      |            | 0.4      |
| $g_{FS*}$                        | Forward Transconductance            | $V_{GS} = 10V$    | $I_D = 200mA$        | 100                       |      | $\mu mhos$ |          |
| <b>DYNAMIC CHARACTERISTICS</b>   |                                     |                   |                      |                           |      |            |          |
| $C_{iss}$                        | Input Capacitance                   | $V_{DS} = 25V$    |                      |                           | 60   | pF         |          |
| $C_{oss}$                        | Output Capacitance                  | $V_{GS} = 0V$     |                      |                           | 25   |            |          |
| $C_{rss}$                        | Reverse Transfer Capacitance        | $f = 1MHz$        |                      |                           | 5    |            |          |
| <b>SWITCHING CHARACTERISTICS</b> |                                     |                   |                      |                           |      |            |          |
| $t_{ON}$                         | Turn–On Time                        | $V_{DD} = 15V$    | $R_L = 25\Omega$     |                           | 10   | ns         |          |
| $t_{OFF}$                        | Turn–Off Time                       | $R_G = 25\Omega$  | $I_D = 600mA$        |                           | 10   |            |          |

\* Pulse Test:  $PW = 300 \mu s$ ,  $\delta \leq 2\%$

| THERMAL CHARACTERISTIC |   | Min. | Typ. | Max.  | Unit          |
|------------------------|---|------|------|-------|---------------|
| $R_{\theta JA}$        | Thermal Resistance, Junction to Ambient |      |      | 312.5 | $^{\circ}C/W$ |